IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	Group Art Unit: 2824
J. P. KOTOWSKI, ET AL.	Examiner: JUNG H. HUR
Application No. 10/067,441	**DECLARATION BY PAUL WERKING IN SUPPORT OF DECLARATION UNDER 37 CFR 1.131 TO OVERCOME CITED PATENT**
Filed: February 4, 2002	
For: **INTEGRATED CIRCUIT AND METHOD FOR TESTING SAME USING SINGLE PIN TO CONTROL TEST MODE AND NORMAL MODE OPERATION**	400 Montgomery Street, Suite 1110 San Francisco, CA 94104 (415) 433-2250

Attorney Docket: NSC1-G9800
[P05051]

Mail Stop Non-Fee Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

1. I, Paul Werking, am an employee of National Semiconductor Corporation ("NSC"), and have read the above-referenced application (the '441 application).

2. Kyle Fodchuk ("Kyle") is one of the two named inventors of the '441 application, and is an employee of NSC. During the year 2002, in the course of my duties for NSC, I worked with Kyle on the design of a low dropout ("LDO") voltage regulator integrated circuit that implements the invention of the '441 application (the "Invention").

3. NSC has manufactured and tested several prototypes of the LDO voltage regulator circuit. Two early integrated circuit prototypes of the LDO voltage regulator circuit embody the Invention, including one known to NSC personnel as the "Hobbs 2" circuit and a later one known to NSC personnel as the "Hobbs 3" circuit. The portion of the Hobbs 2 circuit that implements the Invention is known to NSC personnel as the "OnePin circuit." The portion of the Hobbs 3 circuit that implements the Invention is also known to NSC personnel as the "OnePin circuit."

4. During January 2002, including on January 8, 2002, and January 14, 2002, Kyle worked on the design of the Hobbs 2 circuit, including the design of its OnePin circuit, at NSC's facility in Grass Valley, California. Kyle and I attended a meeting on January 8, 2002, at which the design of the Hobbs 2 circuit (including its OnePin circuit) was discussed by NSC personnel. On January 14, 2002, Kyle's engineering group at NSC (to which I also belonged) submitted specifications for manufacturing the Hobbs 2 circuit to an NSC chip fabrication facility in Texas. On January 17, 2002, the layout for the Hobbs 2 circuit was placed on a reticle in accordance with these specifications. Using this reticle (during January 18, 2002 to February 19, 2002), the Hobbs 2 circuit and other integrated circuits were manufactured at the NSC chip fabrication facility in Texas on each wafer of a wafer lot known within NSC as the "Saturn35" wafer lot. On each wafer of the Saturn35 wafer lot, the die that embodies the Hobbs 2 circuit is referred to by NSC as the "S35V20HA1" die.

5. Attached Exhibit A is a copy of an e-mail message to me that I received from an NSC employee on January 18, 2002, documenting that the layout for the Hobbs 2 chip had been placed on a reticle as of January 17, 2002.

6. Attached Exhibit B is a diagram of a wafer of the Saturn35 wafer lot, showing the die (labeled "S35V20HA1") that embodies the Hobbs 2 circuit, and also showing other dies on the wafer. Attached Exhibit C is a listing of the dies on each wafer of the Saturn35 wafer lot.

7. During January 8, 2002, through February 4, 2002, Kyle worked diligently and reasonably continuously, at NSC's facility in Grass Valley, California, on the design of the OnePin circuit of the Hobbs 2 circuit and the design of an improved version of the OnePin circuit of the Hobbs 2 circuit. On February 5, 2002, Kyle and I (and other NSC personnel) attended a meeting at NSC's facility in Grass Valley, California, at which Kyle presented and discussed modifications to the OnePin circuit (of the Hobbs 2 chip) that he had designed and that he proposed for implementation in the OnePin circuit of the Hobbs 3 chip.

8. During February 2002, my engineering group at NSC received several of the

manufactured Hobbs 2 circuits, each packaged in a T0220 package. Also during February 2002, Kyle programmed five of the Hobbs circuits and the five programmed Hobbs 2 circuits were tested on an automatic tester at one of NSC's facilities in the U.S. Also during February 2002, Kyle and I performed and/or supervised additional testing of a number of the Hobbs 2 circuits.

9. I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Executed on: _June 11, 2003_   By:_____
                                      PAUL WERKING

Exhibit A

Mary Anne Nigro
01/18/02 10:04 AM

   To: James C Schmoock/Americas/NSC@NSC, Paul Werking/Americas/NSC@NSC
      cc:
   Subject: Saturn35 array

Jim and Paul,

FYI !!

Mary Anne

--------------------- Forwarded by Mary Anne Nigro/Americas/NSC on 01/18/2002
10:06 AM ---------------------------

Peter Misich
01/18/2002 09:57 AM
To: Scott D Carper/Americas/NSC@NSC, Keith B Schoendoerfer/Americas/NSC@NSC,
Mary Anne Nigro/Americas/NSC@NSC, Raj Singh/Contractor/Americas/NSC@NSC, Mark J
Mercer/Americas/NSC@NSC, Richard Marks/Americas/NSC@NSC, Paul
Reyes/Americas/NSC@NSC
cc: Thuan Duong/Americas/NSC@NSC, Kenneth Chong/Americas/NSC@NSC

Subject: Saturn35 array

Hello all,
The Saturn35 reticle array map and die list are ready for your review.
Rgds,
Peter

--------------------- Forwarded by Peter Misich/Americas/NSC on 01/18/2002
09:46 AM ---------------------------

Thuan Duong
01/17/2002 06:14 PM
To: Peter Misich/Americas/NSC@NSC
cc: Thuan Duong/Americas/NSC

Subject: Saturn35 array

Hi Peter,
Here are saturn35 array and device diesizes, pls, review.
Thanks,
Thuan

S35LM3819A8
S35LM3819C1
S35LM3819B1
S35PM2LMV1
S35PMD2LMV1

TSAT5502
TSAT5502
TSAT5502
TSAT5502
S35LM9843A
S35LM4879A
TSAT5501
TSAT5501
TSAT5501
TSAT5501

S35EMPIREA1
S35EMPIREA1
S35EMPIREA1
S35V20HA1
S35PM2LMV1
S35PMD2LMV1

S35G29651N3
S35G29651N5
S35G29651P3
TSAT5504
TSAT5504
TSAT5503
S35V20HA1
S35PM2LMV1
S35PMD2LMV1

S35PSD2LMV1
S35PSD2LMV1
S35PSD2LMV1
S35PLV2LMV1
S35PLV2LMV1
TSAT5504
TSAT5503
S35LM9843A
S35LM4879A
S35G29651N3
S35G29651N3

TSAT5503
S35LM9843A
S35LM4879A
S35G29651P3
S35G29651P3

TSAT5503
S35LM9843A
S35LM4879A
S35G29651N5
S35G29651N5

S35G29651P5
S35G29651P5

SATURN35 DIESIZE

EXHIBIT C

	DEVICE NAME	REQUESTOR	#	PHONE	XFW-/+	XFW-/+	SC	XSZ-/+	YSZ-/+	XFINAL	YFINAL	Proc.
1	S35PM2LMV1	S.CARPER	3	16395	991.0	859.0	0.72	713.16	678.12	1426.3	1236.2	sgvr2
2	S35PLV2LMV1	S.CARPER	3	16395	991.0	859.0	0.72	713.16	678.12	1426.3	1236.2	sgvr2
3	S35PSD2LMV1	S.CARPER	3	16395	991.0	859.0	0.72	713.16	678.12	1426.3	1236.2	sgvr2
4	S35PMD2LMV1	S.CARPER	3	16395	991.0	859.0	0.72	713.16	678.12	1426.3	1236.2	sgvr2
5	S35G29651P5	K.SCHOENDOERFER	2	82746556	899.0	511.0	0.72	646.92	367.56	1293.8	735.1	sg2
6	S35G29651N5	K.SCHOENDOERFER	3	82746556	899.0	511.0	0.72	646.92	367.56	1293.8	735.1	sg2
7	S35G29651N3	K.SCHOENDOERFER	3	82746556	899.0	511.0	0.72	646.92	367.56	1293.8	735.1	sg2
8	S35G29651P3	K.SCHOENDOERFER	3	82746556	899.0	511.0	0.72	646.92	367.56	1293.8	735.1	sg2
9	S35LM3819C1	K.SCHOENDOERFER	2	82746556	1446.0	1093.0	0.72	1040.76	786.60	2081.5	1573.2	sg3
10	S35LM3819B1	K.SCHOENDOERFER	2	82746556	1446.0	1093.0	0.72	1040.76	786.60	2081.5	1573.2	sg3
11	S35LM3819A8	K.SCHOENDOERFER	2	82746556	1446.0	1093.0	0.72	1040.76	786.60	2081.5	1573.2	sg3
12	S35EMPIREA1	M.NIGRO	3	82743076	1469.0	1060.0	0.72	1057.32	762.84	2114.6	1525.7	sg2
13	S35V20HA1	M.NIGRO	2	82743076	1704.0	1062.0	0.72	1226.52	764.28	2453.0	1528.6	sg2
14	S35LM9843A	R.SINGH	3	12738	968.0	968.0	0.72	696.60	696.60	1422.4	1422.4	sp2
15	S35LM4879A	R.SINGH	3	12738	968.0	968.0	0.72	696.60	696.60	1422.4	1422.4	sp2
16	TSAT3501	M.MERCER	4	87512382	797.0	656.0	0.72	573.48	471.96	1147.0	943.9	sg2
17	TSAT3502	R.MARKS	4	87512382	825.0	589.0	0.72	593.64	423.72	1187.3	847.4	sgvr3
18	TSAT3503	P.REYES	4	87512382	1367.0	774.0	0.72	983.88	556.92	1967.8	1113.8	sgvr3
19	TSAT3504	R.MARKS	3	87512382	825.0	589.0	0.72	593.64	423.72	1187.3	847.4	sgvr3

Note: process s2 = cs65s-2lm, sg2 = cs65sg-2lm, sg3 = cs65sg-3lm, sgvr2 = cs65sgvr-2lm, sgvr3= cs65sgvr-3lm

sp2 = cs65sp-2lm, sp3 = cs65sp-3lm.   # = number of die on reticle.